

Silicon PNP Power Transistors

2SB655

DESCRIPTION

- With TO-3 package
- Low collector saturation voltage
- High power dissipation

APPLICATIONS

- Power amplifier applications
- Recommended for high-power high-fidelity audio frequency amplifier output stage

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

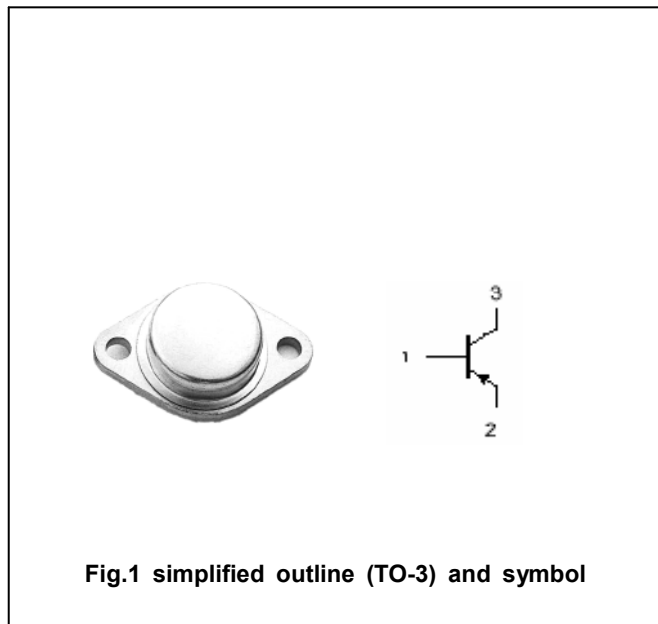


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-160	V
V _{CEO}	Collector-emitter voltage	Open base	-160	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-12	A
I _{CM}	Collector current-peak		-20	A
P _C	Collector power dissipation	T _C =25□	100	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-40~150	□

Silicon PNP Power Transistors

2SB655

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-30mA ; I _B =0	-160			V
V _{(BR)CBO}	Collector-emitter breakdown voltage	I _C =-1mA ; I _E =0	-160			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA ; I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-6A ; I _B =-0.6A			-2.5	V
V _{BE}	Base-emitter on voltage	I _C =-1A ; V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-120V ; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-4V ; I _C =0			-0.1	mA
h _{FE-1}	DC current gain	I _C =-1A ; V _{CE} =-5V	35		200	
h _{FE-2}	DC current gain	I _C =-5A ; V _{CE} =-5V	20			
f _T	Transition frequency	I _C =-1A ; V _{CE} =-5V		20		MHz

PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)